200

400

600

800

1000

passivated technology.

400Hz on resistive or inductive load.

ABSOLUTE RATINGS (limiting values)

		204	404	604	804	1004	Unit
Symbol	Parameter				TYN		
TI	Maximum lead temperature for soldering during from case	10 sat 4.5 mm 260			°C		
⊤stg Tj	Storage and operating junction temperature rang	ge - 40 to + 150 - 40 to + 125			℃ ℃		
dl/dt	Critical rate of rise of on-state current Gate supply : $I_G = 100 \text{ mA} \text{ di}_G/\text{dt} = 1 \text{ A/}\mu\text{s}$			100		A/µs	
l <sup>2</sup> t	l <sup>2</sup> t value	tp =	10 ms		18		A <sup>2</sup> s
		tp = 10 ms		60			
ITSM	Non repetitive surge peak on-state current (Tj initial = 25°C)	tp =	8.3 ms		63		A
IT(AV)	Average on-state current (180° conduction angle, single phase circuit)	Tc = 115 °C		2.5			A
IT(RMS)	RMS on-state current (180° conduction angle)	Tc =	115 °C		4		Α

Parameter

This general purpose Family of Silicon Controlled Rectifiers is designed for power supplies up to

Repetitive peak off-state voltage

Tj = 125 °C

The TYN 204 ---> TYN 1004 Family of Silicon Controlled Rectifiers uses a high performance glass

#### **FEATURES**

DESCRIPTION

Symbol

VDRM

VRRM

March 1995

- HIGH SURGE CAPABILITY
- HIGH ON-STATE CURRENT
- HIGH STABILITY AND RELIABILITY

**TO220AB** 

(Plastic)

Value

# SGS-THOMSON MICROELECTRONICS TYN 204 ---> TYN 1004

### SCR

Unit

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#### TYN 204 ---> TYN 1004

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#### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction to ambient	60	•C/W
Rth (j-c) DC	Junction to case for DC	2.5	°C/W

#### GATE CHARACTERISTICS (maximum values)

 $P_{G}(AV) = 1W$   $P_{GM} = 10W$  (tp = 20 µs)  $I_{FGM} = 4A$  (tp = 20 µs)  $V_{RGM} = 5 V$ .

#### ELECTRICAL CHARACTERISTICS

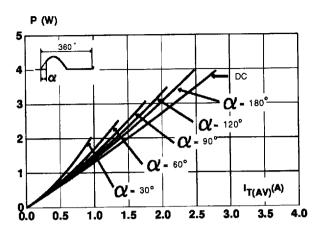
Symbol	Test Conditions			Value	Unit
lGT	V <sub>D</sub> =12V (DC) RL=33Ω	Tj=25°C	MAX	15	mA
VGT	VD=12V (DC) RL=33Ω	Tj=25°C	MAX	1.5	v
VGD	VD=VDRM RL=3.3kΩ	Tj= 110℃	MIN	0.2	v
tgt	VD=VDRM IG = 40mA dIg/dt = 0.5A/µs	Tj=25°C	ТҮР	2	μs
١L	IG= 1.2 IGT	Tj=25°C	ТҮР	50	mA
ŀн	lγ= 100mA gate open	Tj=25°C	MAX	30	mA
∨тм	ITM= 8A tp= 380µs	Tj=25°C	MAX	1.8	v
IDRM IRRM	V <sub>DRM</sub> Rated V <sub>RRM</sub> Rated	Tj=25℃	MAX	0.01	mA
		Tj= 110°C		2	
d∨/dt	Linear slope up to VD=67%VDRM gate open	Tj= 110℃	MIN	200	V/µs
tq	VD=67%VDRM ITM=8A VR=25V dITM/dt=30 A/μs dVD/dt=50V/μs	Tj= 110℃	ТҮР	70	μs

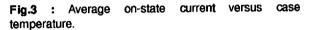


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Fig.1 : Maximum average power dissipation versus average on-state current.

Fig.2 : Correlation between maximum average power dissipation and maximum allowable temperatures ( $T_{amb}$  and  $T_{case}$ ) for different thermal resistances heatsink + contact.





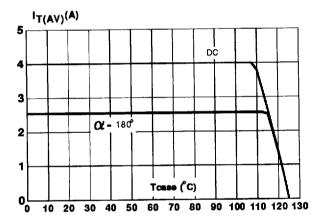
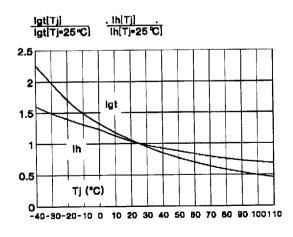


Fig.5 : Relative variation of gate trigger current versus junction temperature.



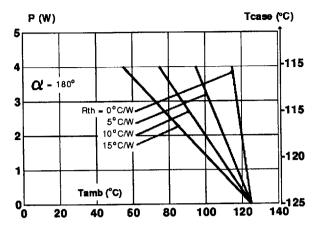


Fig.4: Relativa variation of thermal impedance versus pulse duration.

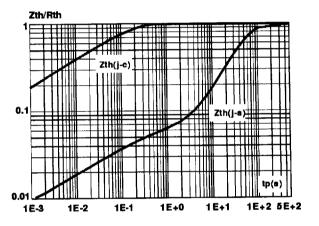
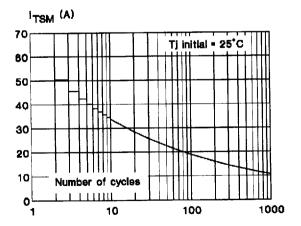


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.

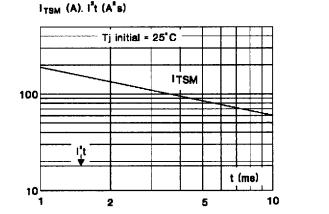


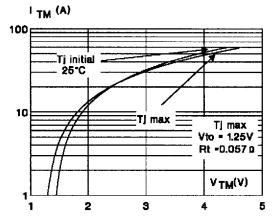


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**Fig.7**: Non repetitive surge peak on-state current for a sinusoidal pulse with width :  $t \le 10$  ms, and corresponding value of  $l^2t$ .

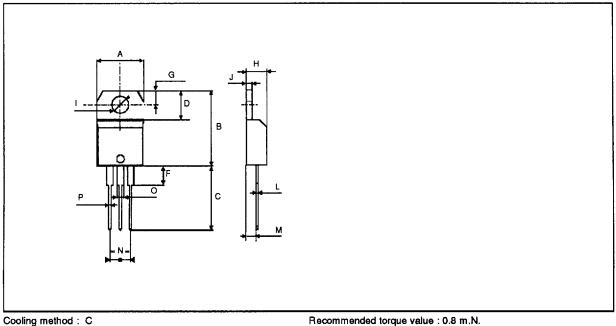
Fig.8 : On-state characteristics (maximum values).





PACKAGE MECHANICAL DATA

**TO220AB** Plastic



Marking : type number Weight : 2.3 g Recommended torque value : 0.8 m.N. Maximum torque value : 1 m.N.

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